

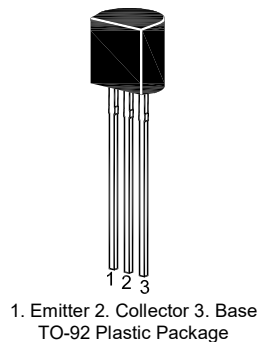
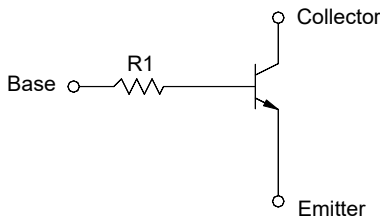
RC110S...RC114S

NPN Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{Stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	h_{FE}	120	-	-	-
Collector Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	-	100	nA
Emitter Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	-	100	nA
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Transition Frequency at $V_{CE} = 10\text{ V}$, $I_C = 5\text{ mA}$	f_T	-	250	-	MHz
Input Resistor	RC110S	-	4.7	-	K Ω
	RC111S	-	10	-	
	RC112S	-	100	-	
	RC113S	-	22	-	
	RC114S	-	47	-	

